

Supplementary

MXene/NiO Composites for Chemiresistive-Type Room Temperature Formaldehyde Sensor

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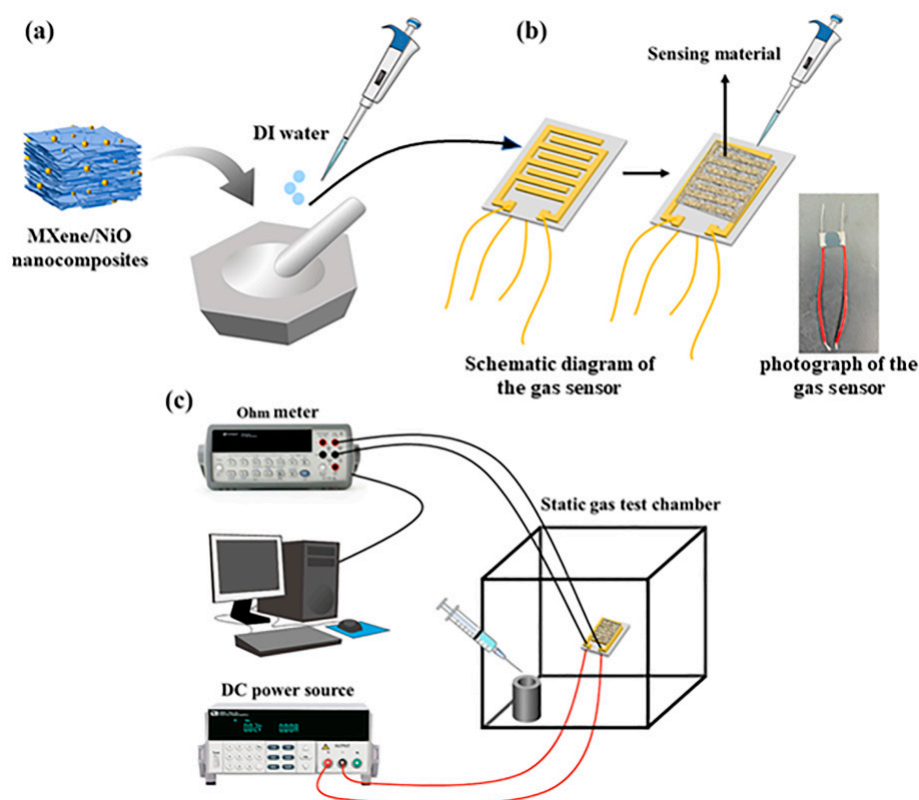


Figure S1. (a) Schematic illustration of the synthesis process of the sensing material (b) Schematic diagram and photograph of the gas sensor. (c) Schematic diagram of the static testing system.

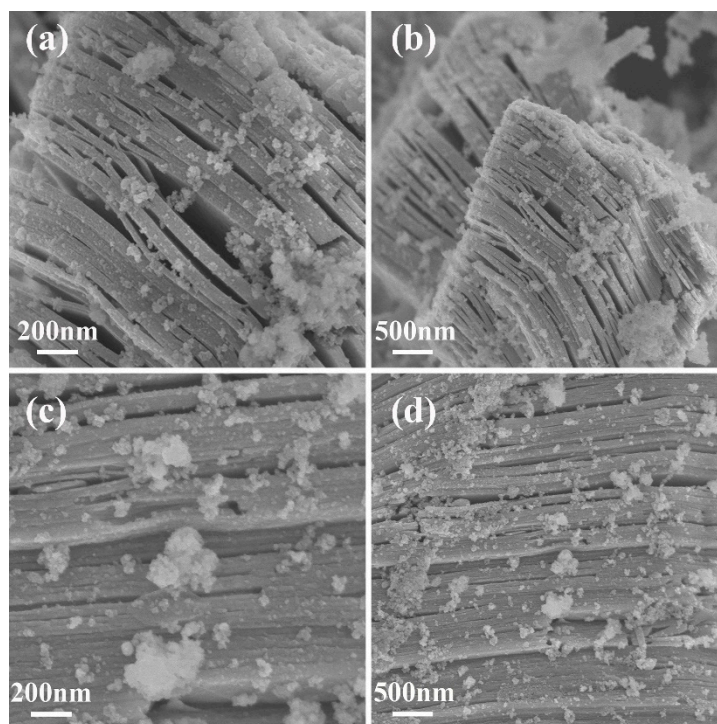


Figure S2. SEM images of (a,b) MXene/NiO-P1 and (c,d)MXene/NiO-P3.

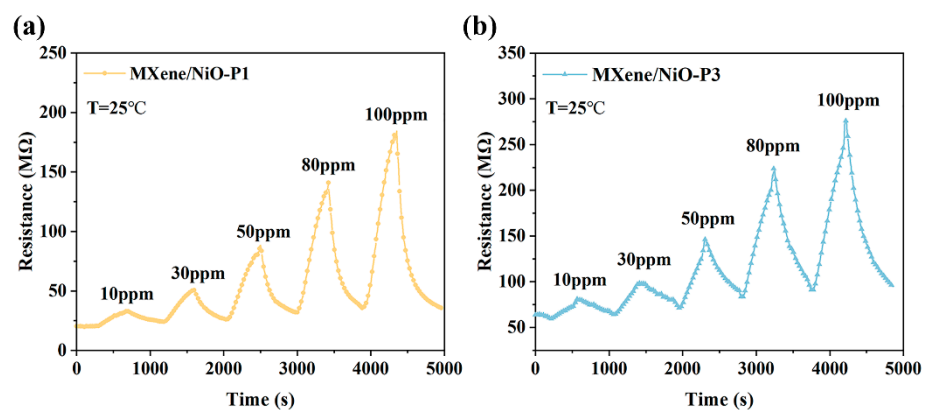


Figure S3. Real-time resistance changes of the sensors based on (a) MXene/NiO-P1 and (b) MXene/NiO-P3 to 10–100 ppm HCHO at 25 °C and RH=40%.

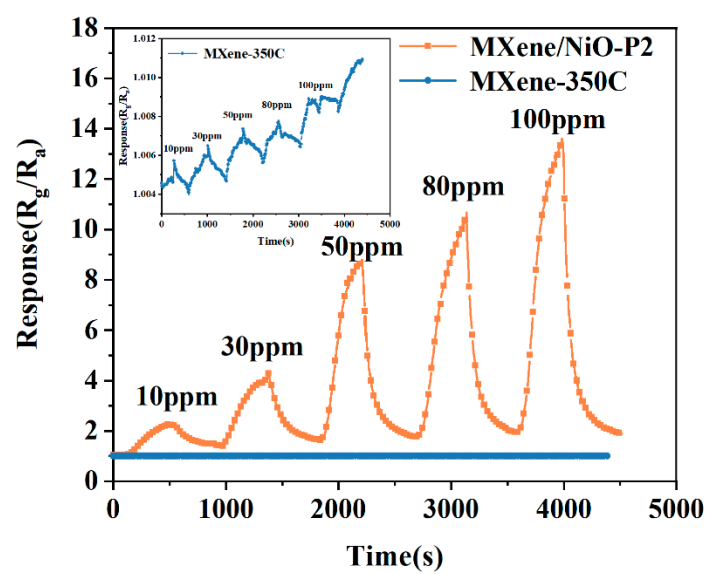


Figure S4. Response changes of the sensors based on MXene/NiO-P2 and MXene-350C to 10–100 ppm HCHO at 25 °C and RH=40%.